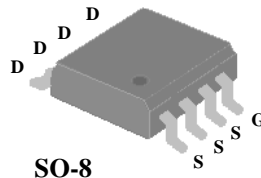




- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ Low On-resistance
- ▼ RoHS Compliant

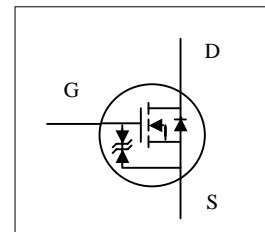


BV_{DSS}	25V
$R_{DS(ON)}$	8.5m Ω
I_D	14A

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.

The SO-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	25	V
V_{GS}	Gate-Source Voltage	± 16	V
$I_D@T_A=25^\circ C$	Continuous Drain Current ³	14	A
$I_D@T_A=70^\circ C$	Continuous Drain Current ³	11	A
I_{DM}	Pulsed Drain Current ¹	50	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient ³	Max. 50	$^\circ C/W$



AP4880GEM

Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	25	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^{\circ}\text{C}, I_D=1mA$	-	0.03	-	$V/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=14A$	-	-	8.5	$m\Omega$
		$V_{GS}=4.5V, I_D=10A$	-	-	15	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=14A$	-	13.5	-	S
I_{DSS}	Drain-Source Leakage Current ($T_j=25^{\circ}\text{C}$)	$V_{DS}=25V, V_{GS}=0V$	-	-	1	μA
	Drain-Source Leakage Current ($T_j=70^{\circ}\text{C}$)	$V_{DS}=20V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 16V$	-	-	± 30	μA
Q_g	Total Gate Charge ²	$I_D=14A$	-	23	37	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=20V$	-	3.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	17	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=15V$	-	11	-	ns
t_r	Rise Time	$I_D=1A$	-	11	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	36	-	ns
t_f	Fall Time	$R_D=15\Omega$	-	25	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	900	1440	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	490	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	195	-	pF
R_g	Gate Resistance	$f=1.0MHz$	-	2	3	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=2A, V_{GS}=0V$	-	-	1.2	V
t_{rr}	Reverse Recovery Time ²	$I_S=14A, V_{GS}=0V,$	-	45	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	42	-	nC

Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Surface mounted on 1 in^2 copper pad of FR4 board, $t \leq 10\text{sec}$; $125^{\circ}\text{C}/W$ when mounted on Min. copper pad.

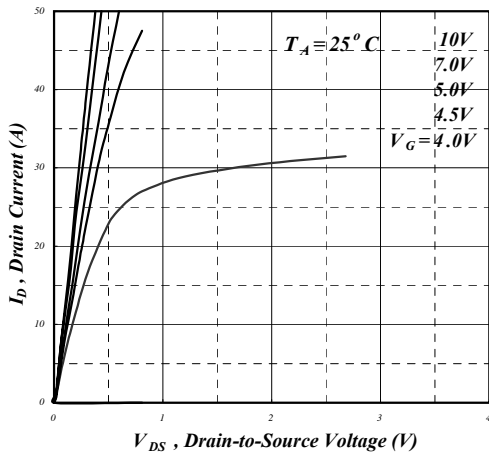


Fig 1. Typical Output Characteristics

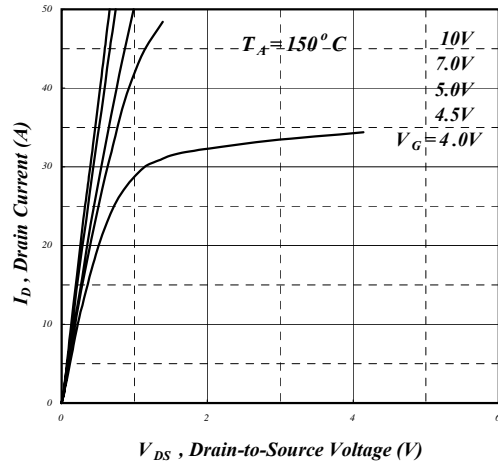


Fig 2. Typical Output Characteristics

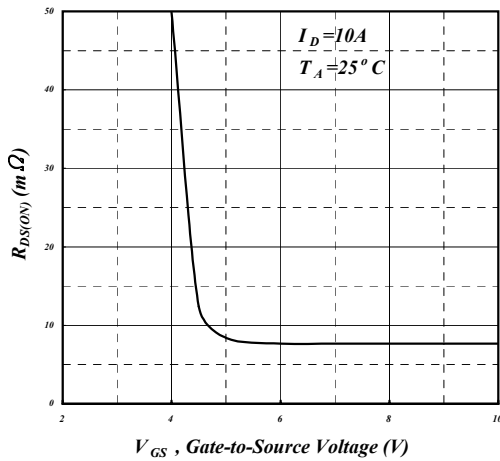


Fig 3. On-Resistance v.s. Gate Voltage

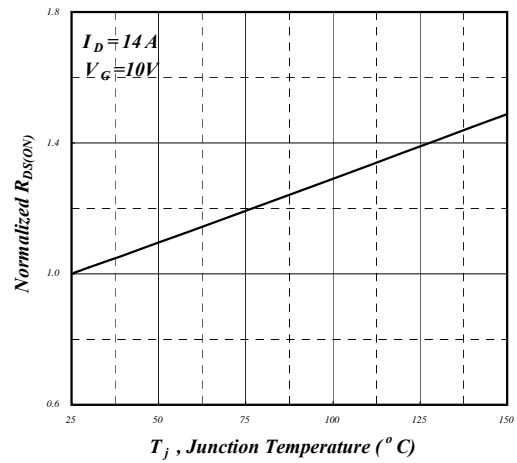


Fig 4. Normalized On-Resistance v.s. Junction Temperature

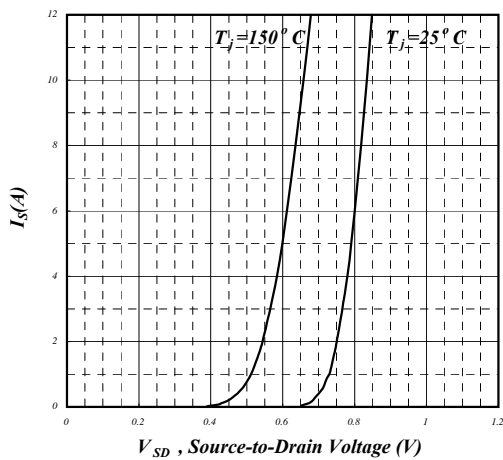


Fig 5. Forward Characteristic of Reverse Diode

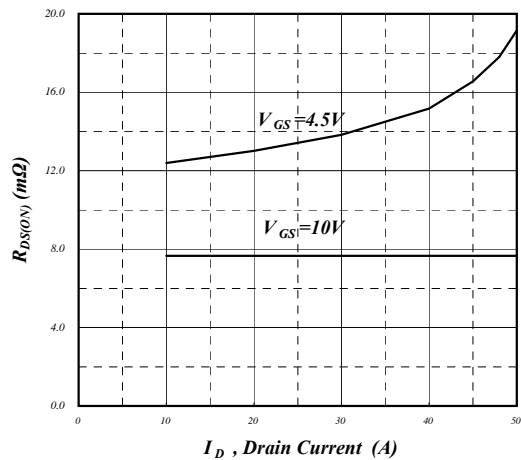


Fig 6. On-Resistance vs. Drain Current

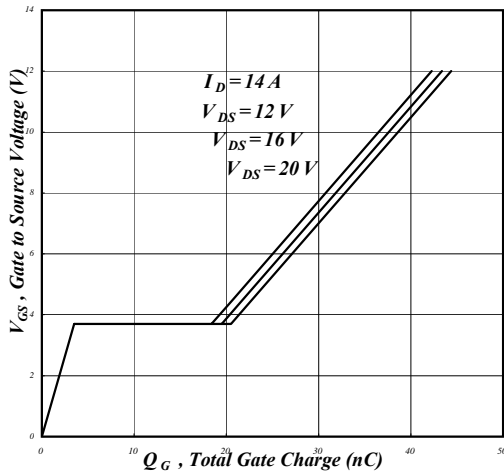


Fig 7. Gate Charge Characteristics

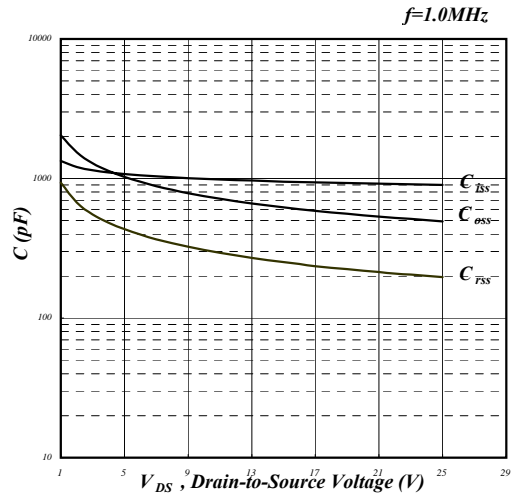


Fig 8. Typical Capacitance Characteristics

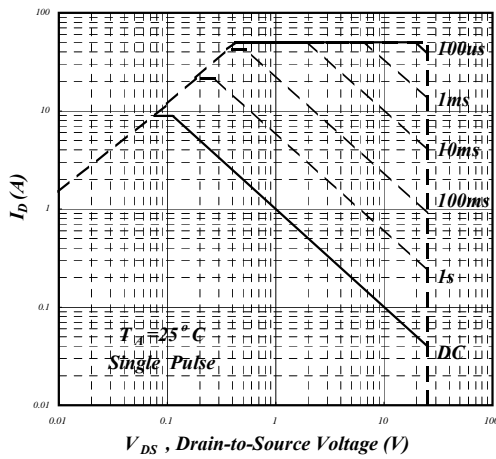


Fig 9. Maximum Safe Operating Area

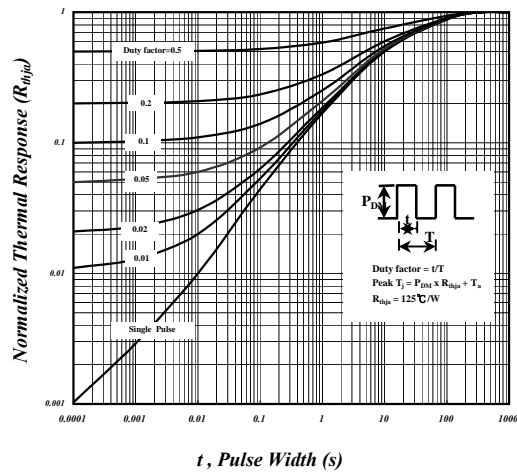


Fig 10. Effective Transient Thermal Impedance

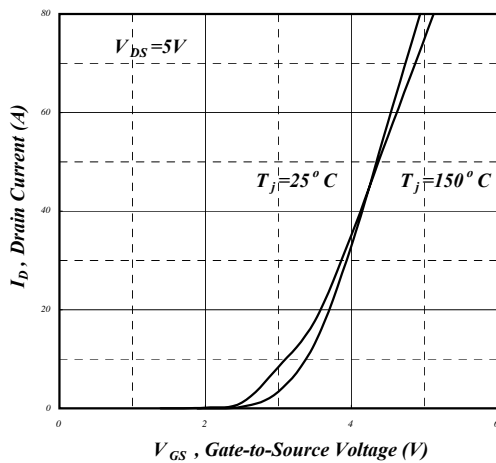


Fig 11. Transfer Characteristics

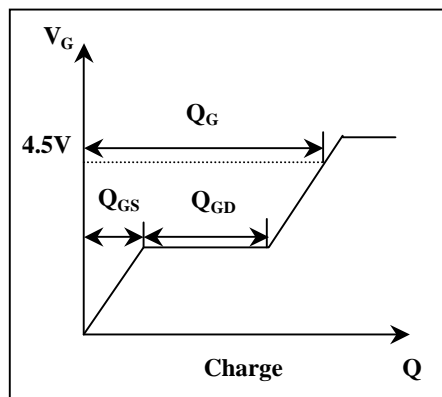


Fig 12. Gate Charge Waveform